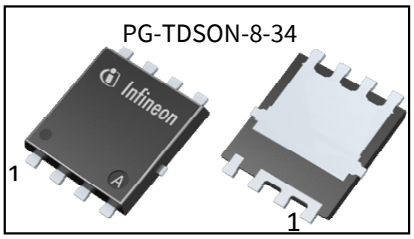
Automotive MOSFET

OptiMOS™-5 Power-Transistor

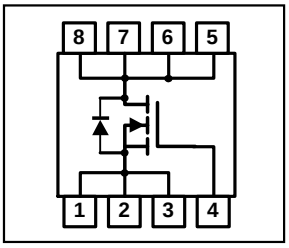
RoHS Infineon Automotive Quality AEC Qualified

PG-TDSON-8-34



Features

- OptiMOS™ power MOSFET for automotive applications
- N-channel – Enhancement mode – Normal Level
- Extended qualification beyond AEC-Q101
- Enhanced electrical testing
- Robust design
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green product (RoHS compliant)
- 100% Avalanche tested



Potential applications

General automotive applications.

Product validation

Qualified for automotive applications. Product validation according to AEC-Q101.

Product Summary

V_{DS}	60	V
$R_{DS(on)}$	2.24	mΩ
I_D (chip limited)	170	A

Type	Package	Marking
IAUC120N06S5N022	PG-TDSON-8-34	5N06N022

Table of Contents

Maximum ratings

at Tj=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	V_{GS}=10 V, Chip limitation[1,2)]	170	A
		V_{GS}=10V, DC current[3)]	120	
		T_a=85 °C, V_{GS}=10 V, R_{thJA} on 2s2p[2,4)]	30	
Pulsed drain current[2)]	$I_{D,pulse}$	T_C=25 °C, t_p= 100 µs	568	
Avalanche energy, single pulse[2)]	E_{AS}	I_D=60 A	174	mJ
Avalanche current, single pulse	I_{AS}	–	120	A
Gate source voltage	V_{GS}	–	±20	V
Power dissipation	P_{tot}	T_C=25 °C	136	W
Operating and storage temperature	T_j, T_{stg}	–	-55 ... +175	°C
IEC climatic category; DIN IEC 68-1	–	–	55/175/56	

Thermal characteristics[2)]

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	–	–	–	1.10	K/W
Thermal resistance, junction - ambient[4)]	R_{thJA}	–	–	23.7	–	

Electrical characteristics

at Tj=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0 V, I_D=1 mA	60	–	–	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=65 µA	2.2	2.8	3.4	
Zero gate voltage drain current	I_{DSS}	V_{DS}=60 V, V_{GS}=0 V, T_j=25 °C	–	–	1	µA
		V_{DS}=60 V, V_{GS}=0 V, T_j=100 °C[2)]	–	–	100	
Gate-source leakage current	I_{GSS}	V_{GS}=20 V, V_{DS}=0 V	–	–	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=7 V, I_D=30 A	–	2.32	2.80	mΩ
		V_{GS}=10 V, I_D=60 A	–	1.90	2.24	
Gate resistance[2)]	R_G	–	–	1.4	–	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics[2]						
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=30 V, f=1 MHz	–	3792	4930	pF
Output capacitance	C_{oss}		–	803	1044	
Reverse transfer capacitance	C_{rss}		–	38	57	
Turn-on delay time	$t_{d(on)}$	V_{DD}=30 V, V_{GS}=10 V, I_D=60 A, R_G=3.5 Ω	–	9	–	ns
Rise time	t_r		–	5	–	
Turn-off delay time	$t_{d(off)}$		–	16	–	
Fall time	t_f		–	11	–	
Gate Charge Characteristics[2]						
Gate to source charge	Q_{gs}	V_{DD}=30 V, I_D=60 A, V_{GS}=0 to 10 V	–	16	21	nC
Gate to drain charge	Q_{gd}		–	9	14	
Gate charge total	Q_g		–	52	68	
Gate plateau voltage	$V_{plateau}$		–	4.7	–	V
Reverse Diode						
Diode continous forward current[2]	I_S	T_C=25 °C	–	–	120	A
Diode pulse current[2]	$I_{S,pulse}$	T_C=25 °C, t_p= 100 µs	–	–	558	
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=60 A, T_j=25 °C	–	0.8	1.1	V
Reverse recovery time[2]	t_{rr}	V_R=30 V, I_F=50A, di_F/dt =100 A/µs	–	43	–	ns
Reverse recovery charge[2]	Q_{rr}		–	40	–	nC

[1] Practically the current is limited by the overall system design including the customer-specific PCB.

[2] The parameter is not subject to production testing – specified by design.

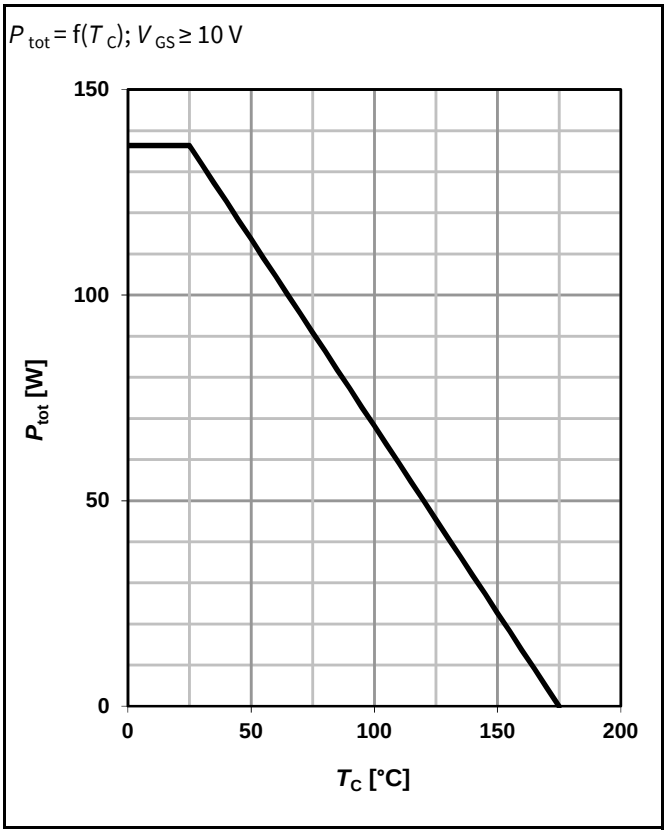
[3] Current is limited by package.

[4] Device on 2s2p FR4 PCB defined in accordance with JEDEC standards (JESD51-5, -7). PCB is vertical in still air.

Electrical characteristics diagrams

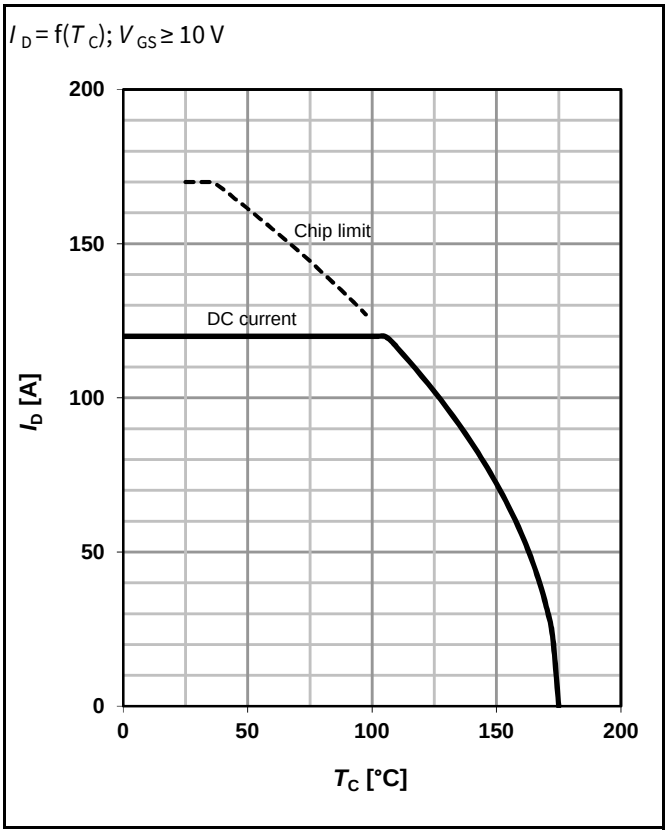
1 Power dissipation

$P_{tot} = f(T_C)$; $V_{GS} \geq 10$ V



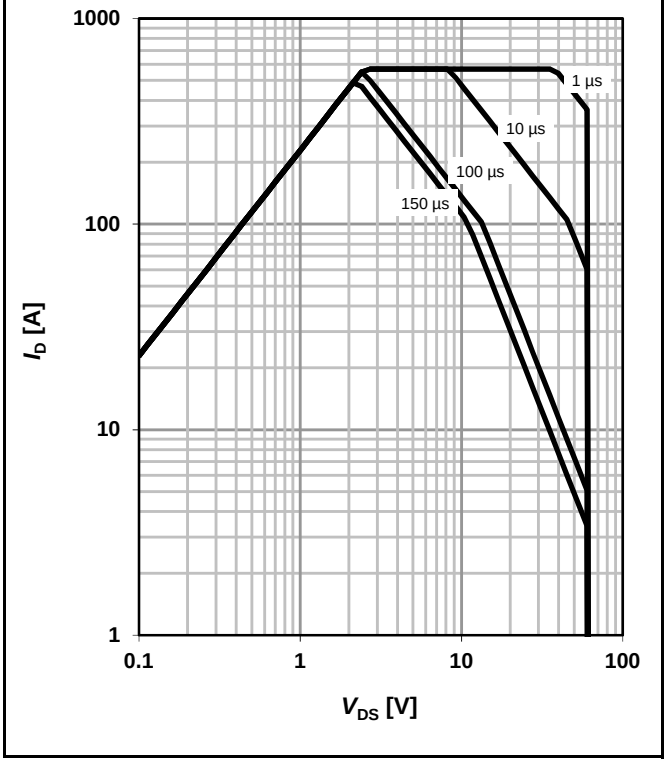
2 Drain current

$I_D = f(T_C)$; $V_{GS} \geq 10$ V



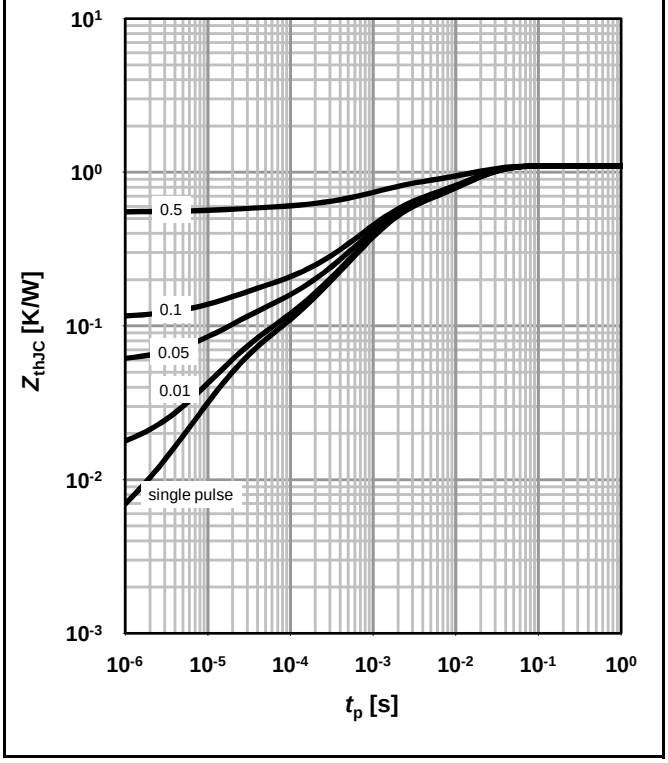
3 Safe operating area

$I_D = f(V_{DS})$; $T_C = 25$ °C; $D = 0$; parameter: t_p



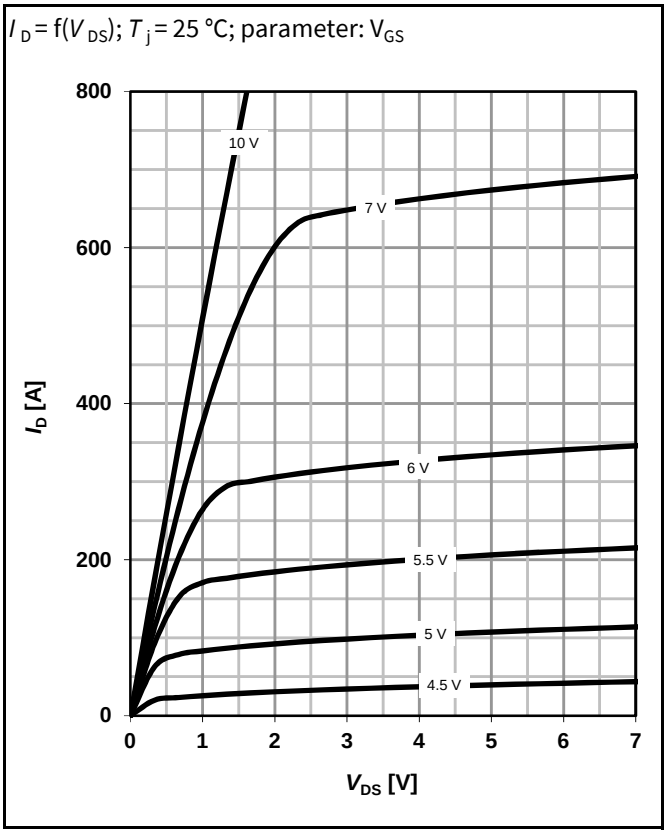
4 Max. transient thermal impedance

$Z_{thJC} = f(t_p)$; parameter: $D=t_p/T$



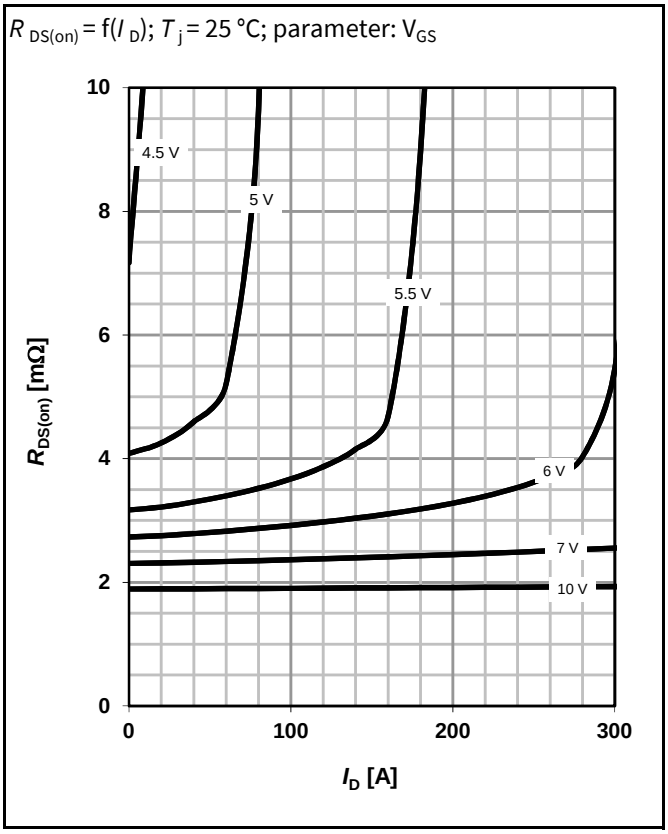
5 Typ. output characteristics

$I_D = f(V_{DS})$; $T_j = 25$ °C; parameter: V_{GS}



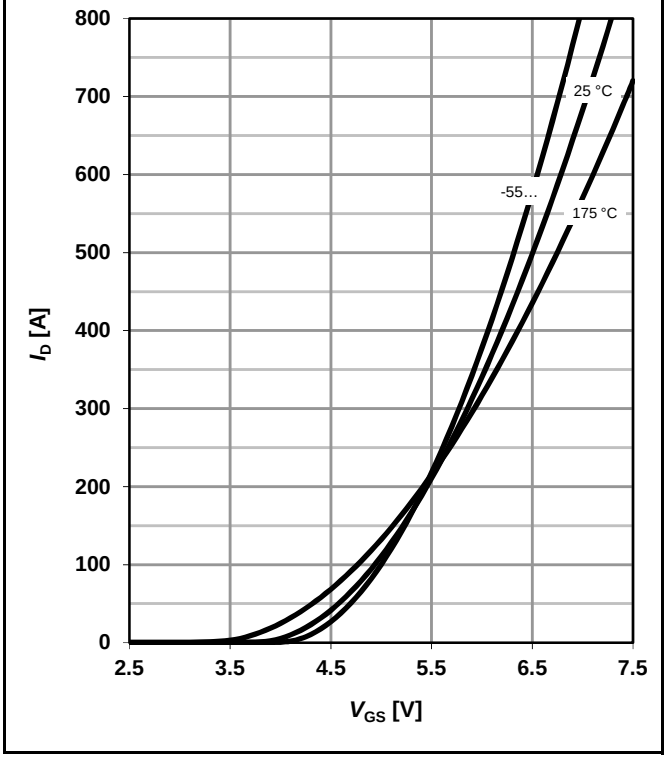
6 Typ. drain-source on-state resistance

$R_{DS(on)} = f(I_D)$; $T_j = 25$ °C; parameter: V_{GS}



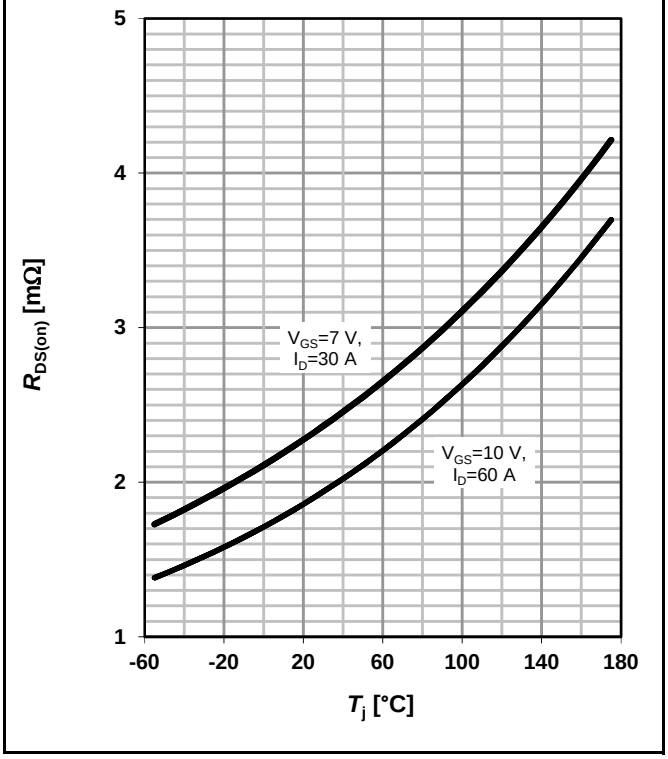
7 Typ. transfer characteristics

$I_D = f(V_{GS})$; $V_{DS} = 6$V: parameter: T_j



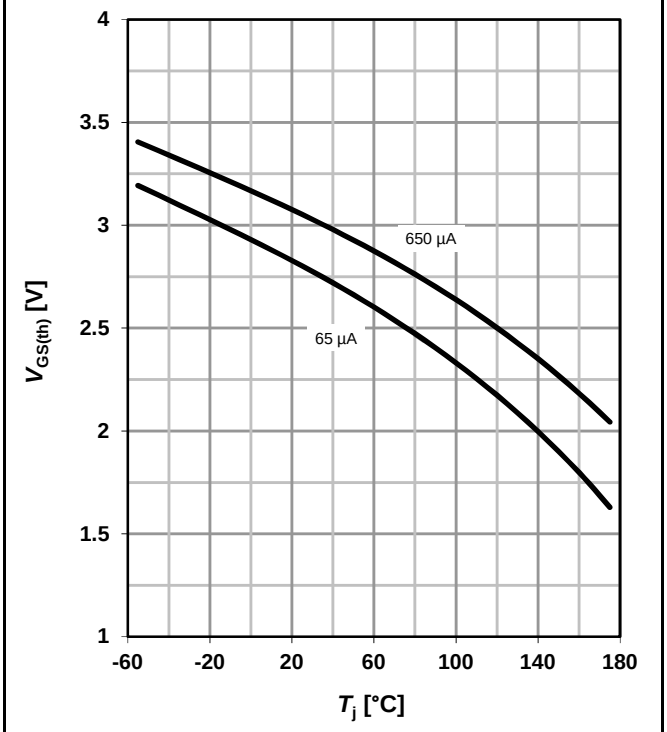
8 Typ. drain-source on-state resistance

$R_{DS(on)} = f(T_j)$; parameter: I_D, V_{GS}



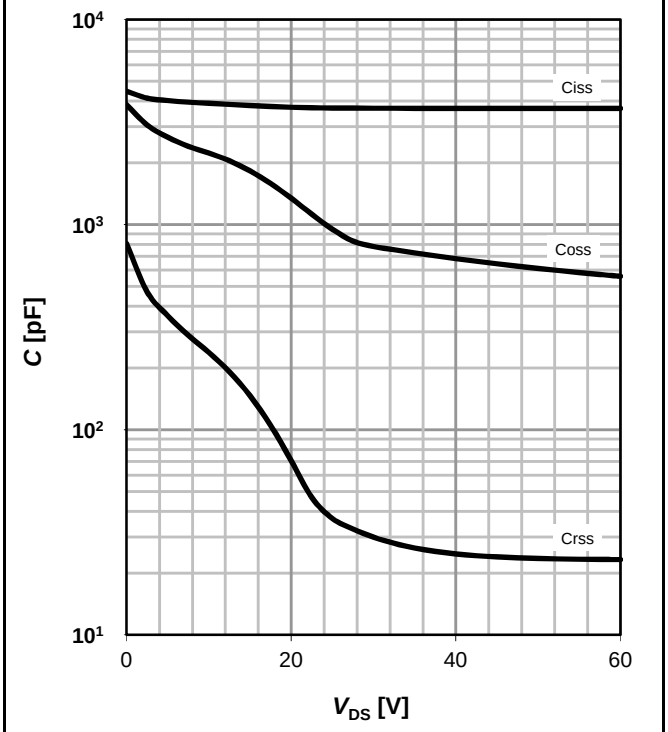
9 Typ. gate threshold voltage

$V_{GS(th)} = f(T_j)$; $V_{GS} = V_{DS}$; parameter: I_D



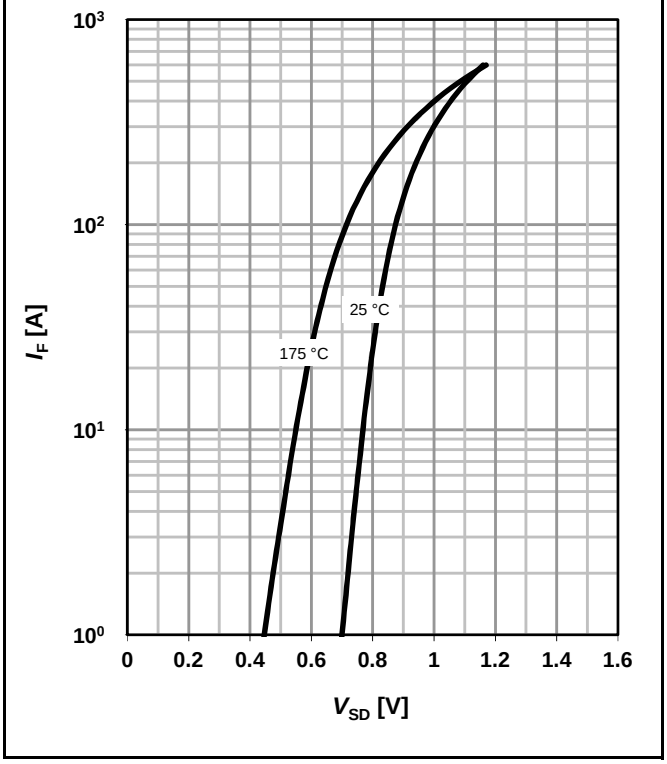
10 Typ. capacitances

$C = f(V_{DS})$; $V_{GS} = 0$ V; $f = 1$ MHz



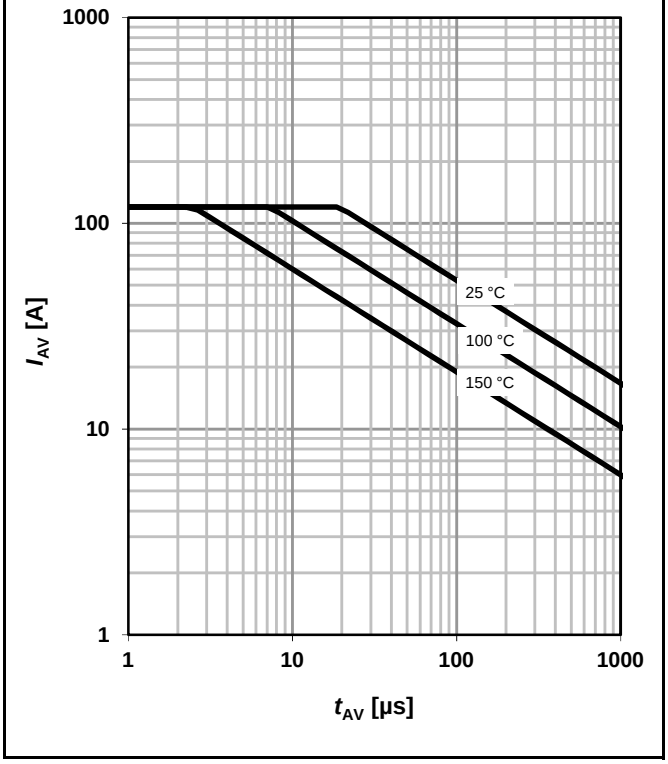
11 Typical forward diode characteristics

$I_F = f(V_{SD})$; parameter: T_j



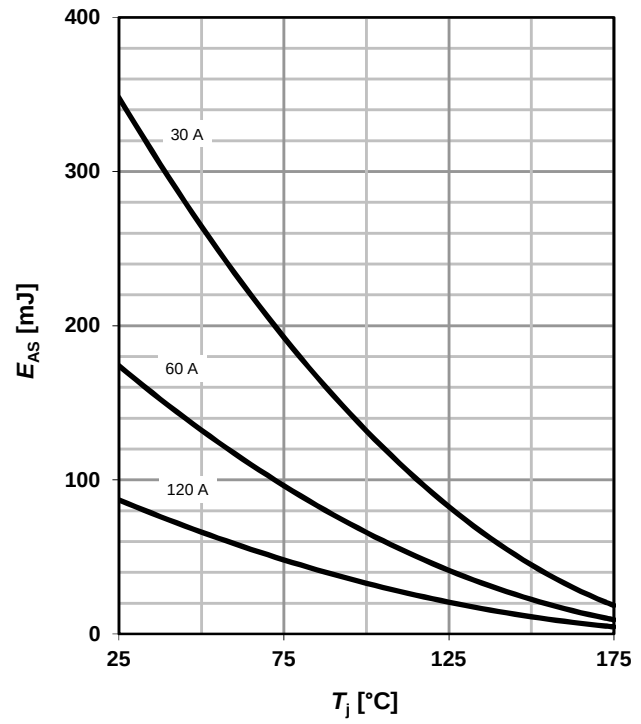
12 Typ. avalanche characteristics

$I_{AS} = f(t_{AV})$; parameter: $T_{j(start)}$



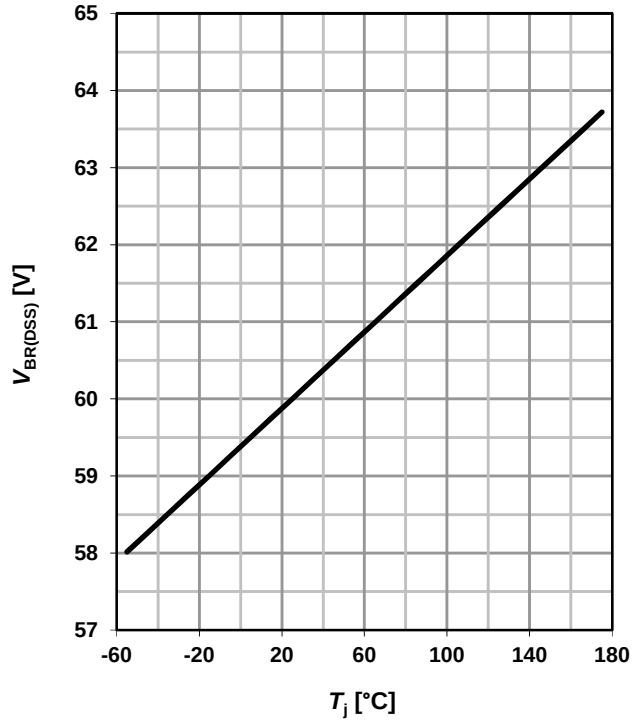
13 Typical avalanche energy

$E_{AS} = f(T_j)$; parameter: ID



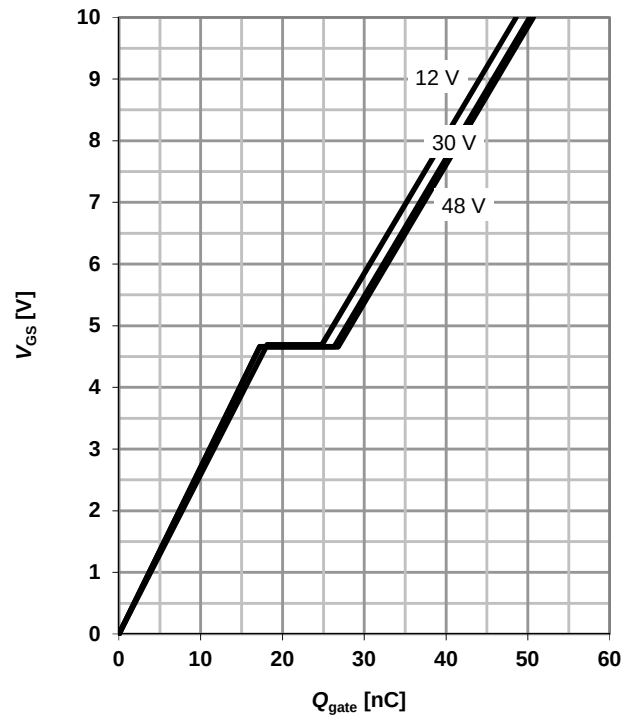
14 Drain-source breakdown voltage

$V_{BR(DSS)} = f(T_j)$; $I_{D\_typ} = 1$ mA

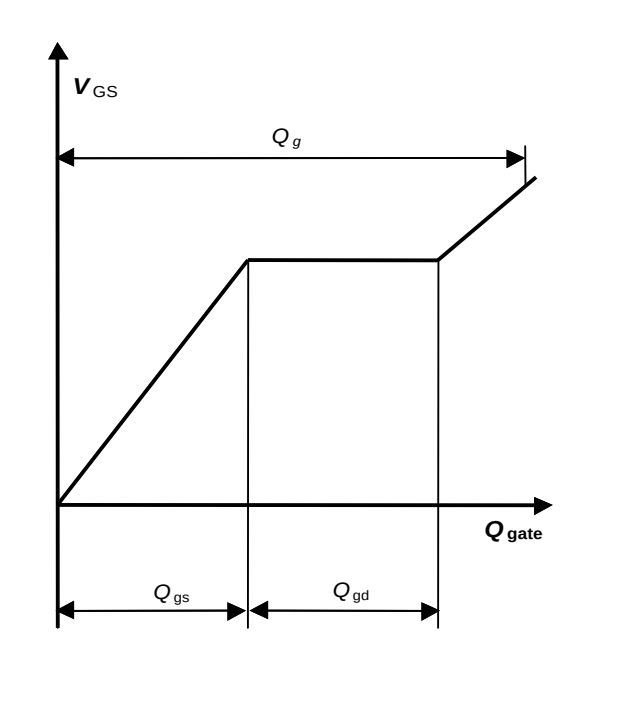


15 Typ. gate charge

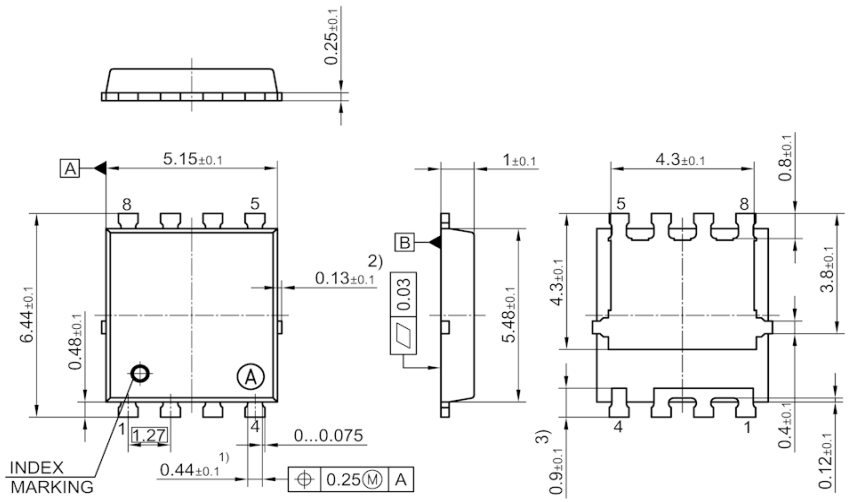
$V_{GS} = f(Q_{gate})$; $I_D = 60$ A pulsed; parameter: V_{DD}



16 Gate charge waveforms

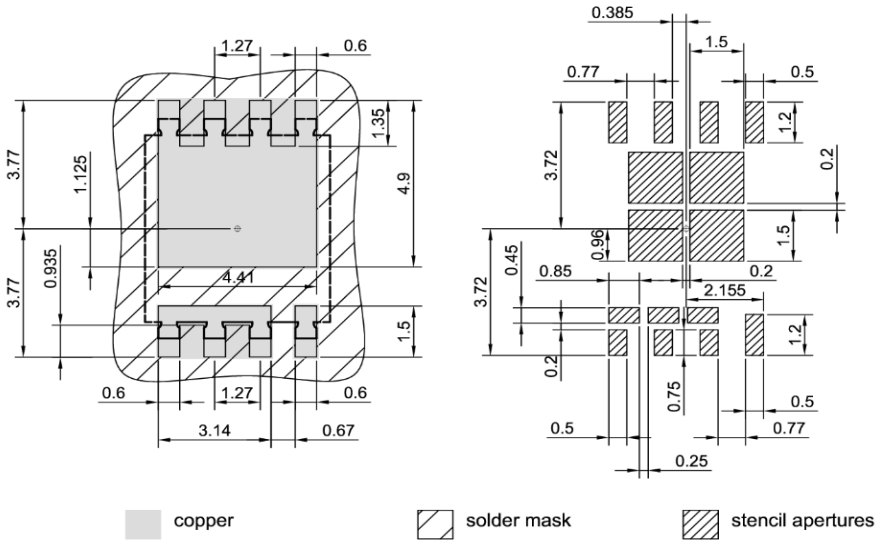


Package Outline



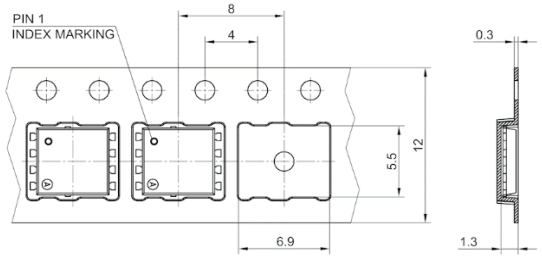
1) EXCLUDE MOLD FLASH
2) REMOVAL ON MOLD GATE, INTRUSION 0.1MM AND PROTRUSION 0.1MM
3) LEAD LENGTH UP TO ANTI FLASH LINE
4)ALL METAL SURFACE ARE PLATED, EXCEPT AREA OF CUT
ALL DIMENSIONS ARE IN UNITS MM
THE DRAWING IS IN COMPLIANCE WITH ISO 128 & PROJECTION METHOD 1 [ ]

Footprint



All dimensions are in units mm

Packaging



ALL DIMENSIONS ARE IN UNITS MM
THE DRAWING IS IN COMPLIANCE WITH ISO 128 & PROJECTION METHOD 1 [ ]

Revision History

Revision	Date	Changes
Revision 1.0	21.06.2022	Final Data Sheet

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFETs ***category:***

Click to view products by Infineon ***manufacturer:***

Other Similar products are found below :

MCH3443-TL-E MCH6422-TL-E PMV32UP215 NTNS3A92PZT5G 2SK2464-TL-E 2SK3818-DL-E 2SJ277-DL-E 2SK2267(Q) AON6932A TS19452CS RL EFC2J004NUZTDG 743-9 US6M2GTR IRF40H233XTMA1 STU5N65M6 DMN13M9UCA6-7 STU7N60DM2 2N7002W-G NTMFS006N08MC NTTFS5C680NLTAG IPB45P03P4L11ATMA2 NVTFS6H880NLWFTAG NTMC083NP10M5L NTTFS022N15MC NVMFS5C420NLWFT1G BXP4N65F BXP2N20L BXP2N65D NTD5C632NLT4G NTMYS2D1N04CLTWG NVD360N65S3T4G NVMTS1D1N04CTXG CJAC130SN06L HSBA6054 HSBB6054 HSBB0210 HSBB0056 HSBA6901 BSC004NE2LS5 BSZ075N08NS5 LBSS138DW1T1G AP0903G SSM10N954L,EFF(S 2SK3878(STA1,E,S) TPN6R303NC,LQ(S AP3N5R0MT AP6NA3R2MT AP3C023AMT AP6242 HSBB3909